

**In the Claims:**

1. (currently amended) An integrated circuit chip mounted on a leadframe, comprising:

a chip having first and second major opposing surfaces and a circuit having active components and having a protective overcoat over the first surface;

a network of substantially coplanar power distribution lines laterally disposed deposited on the first surface of said chip over said overcoat, located directly over active components of said circuit; ~~and~~ said lines conductively ~~and vertically~~ connected to selected active components below said lines in a direction normal to said first surface through vias in said overcoat, said lines also connected ~~and also~~ by conductors ~~connected~~ to segments of said leadframe, and

an electrically conductive member directly connecting said power distribution lines to connection regions external of said chip.

~~thereby saving silicon real estate consumed by circuit power distribution lines and conductor pads, gaining circuit design flexibility and assembly manufacturability, and reducing input/output numbers of said segments.~~

2. (currently amended) A semiconductor device having an additional conductor network on the chip surface, wherein the power distribution of the integrated circuit is combined with the power distribution of the leadframe, comprising:

a semiconductor chip having first and second opposing major surfaces surfaces;

an integrated circuit fabricated on said first chip surface, said circuit having active components, contact pads, at least one metal layer, and being protected by a mechanically strong, electrically insulating overcoat having a plurality of metal-filled vias to contact said at least one metal layer;

electrically conductive substantially coplanar, laterally disposed films deposited on said overcoat and patterned into a network of lines substantially vertically over said active components, said films in contact with said vias and having at least one stress-absorbing film and an outermost film being non-corrodible and metallurgically attachable;

said network patterned to distribute power current and ground potential;

a leadframe having a chip mount pad, a first plurality of segments providing electrical signals, and a second plurality of segments providing electrical power and ground;

said second chip surface attached to said chip mount pad;

electrical conductors connecting said contact pads with said first plurality of segments; and

electrical conductors connecting said network lines with said second plurality of segments.

3. (previously presented) The device according to Claim 2 wherein said chip is selected from a group consisting of silicon, silicon germanium, gallium arsenide, and any other semiconductor material customarily used in electrical device fabrication.

4. (canceled)

5. (previously presented) The device according to Claim 2 wherein said integrated circuit comprises multi-layer metallization, at least one of said layers made of pure or alloyed copper, aluminum, nickel, or refractory metals.

6. (previously presented) The device according to Claim 2 wherein said overcoat comprises materials selected from a group consisting of silicon nitride, silicon oxynitride, silicon carbon alloys, polyimide, and sandwiched films thereof..

7. (previously presented) The device according to Claim 2 wherein said leadframe comprises a sheet-like material selected from a group consisting of copper, copper alloy, aluminum, iron-nickel alloy, or invar.

8 –9 (canceled).

10. (currently amended) The device according to Claim 2 & wherein leadframe segments ~~not included in said encapsulation are~~ be shaped as leads solderable to outside parts.

11. (previously presented) The device according to Claim 2 further comprising solder balls attached to said electrical conductors connecting said network lines with said second plurality of segments.

12. (previously presented) The device according to Claim 2 further comprising a wire bond to said electrical conductors connecting said network lines with said second plurality of segments.

13. (previously presented) The device according to Claim 2 wherein said electrically conductive films comprise at least one stress-absorbing metal layer selected from a group consisting of copper, nickel, aluminum, tungsten, titanium molybdenum, chromium, and alloys thereof.

14. (previously presented) The device according to Claim 2 wherein said outermost metal layer is selected from a group consisting of pure or alloyed gold, palladium, silver, platinum, and aluminum.

15. (currently amended) The device according to Claim 2 wherein said conductors are bonding wires ~~or solder balls~~.

16. (previously presented) The device according to Claim 15 wherein said bonding wire is selected from a group consisting of pure of alloyed gold, copper, and aluminum.

17. (canceled)

18. (previously presented) The device according to Claim 2 wherein said network of lines is electrically further connected to selected segments suitable for outside electrical contact.

19. (previously presented) The device according to Claim 2 wherein said network of lines, together with said metal-filled vias, provides the power distribution function between said active circuit components.

20-23 (canceled)

